# HAF1002(L), HAF1002(S)

## Silicon P Channel MOS FET Series
## Power Switching

REJ03G1133-0200
(Previous: ADE-208-586)
Rev.2.00
Sep 07, 2005

### Description

This FET has the over temperature shut-down capability sensing to the junction temperature.

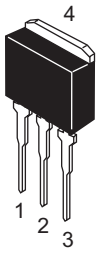
This FET has the built-in over temperature shut-down circuit in the gate area. And this circuit operation to shut-down the gate voltage in case of high junction temperature like applying over power consumption, over current etc.

### Features

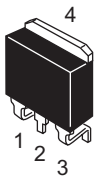
- Logic level operation (–4 to –6 V Gate drive)
- High endurance capability against to the short circuit
- Built-in the over temperature shut-down circuit
- Latch type shut-down operation (Need 0 voltage recovery)

### Outline

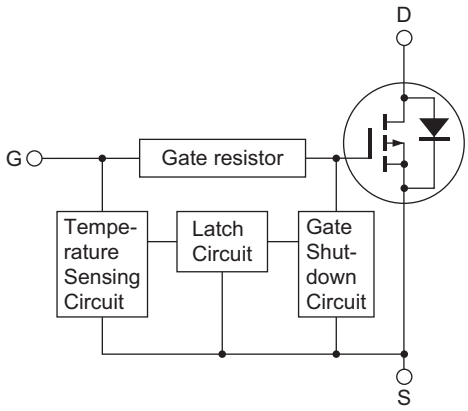
RENESAS Package code: PRSS0004AE-A
(Package name: LDPAK (L) )




RENESAS Package code: PRSS0004AE-B
(Package name: LDPAK (S)-(1) )




1. Gate
2. Drain
3. Source
4. Drain



## Absolute Maximum Ratings

(Ta = 25°C)

| Item | Symbol | Value | Unit |
|---|---|---|---|
| Drain to source voltage | $V_{DSS}$ | –60 | V |
| Gate to source voltage | $V_{GSS}$ | –16 | V |
| | $V_{GSS}$ | 3 | V |
| Drain current | $I_D$ | –15 | A |
| Drain peak current | $I_{D\ (pulse)}$ Note 1 | –30 | A |
| Body-drain diode reverse drain current | $I_{DR}$ | –15 | A |
| Channel dissipation | Pch Note 2 | 50 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | –55 to +150 | °C |

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. Value at Tc = 25°C

## Typical Operation Characteristics

| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|---|---|---|---|---|---|---|
| Input voltage | $V_{IH}$ | –3.5 | — | — | V | |
| | $V_{IL}$ | — | — | –1.2 | V | |
| Input current (Gate non shut down) | $I_{IH1}$ | — | — | –100 | µA | Vi = –8 V, $V_{DS}$ = 0 |
| | $I_{IH2}$ | — | — | –50 | µA | Vi = –3.5 V, $V_{DS}$ = 0 |
| | $I_{IL}$ | — | — | –1 | µA | Vi = –1.2 V, $V_{DS}$ = 0 |
| Input current (Gate shut down) | $I_{IH\ (sd)\ 1}$ | — | –0.8 | — | mA | Vi = –8 V, $V_{DS}$ = 0 |
| | $I_{IH\ (sd)\ 2}$ | — | –0.35 | — | mA | Vi = –3.5 V, $V_{DS}$ = 0 |
| Shut down temperature | Tsd | — | 175 | — | °C | Channel temperature |
| Gate operation voltage | $V_{OP}$ | –3.5 | — | –13 | V | |

## Electrical Characteristics

(Ta = 25°C)

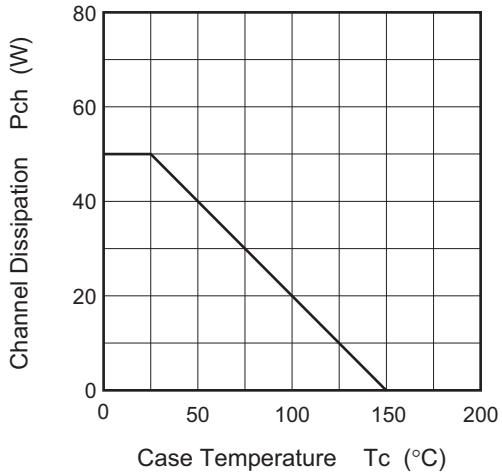
| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|---|---|---|---|---|---|---|
| Drain current | $I_{D1}$ | –7 | — | — | A | $V_{GS}$ = –3.5 V, $V_{DS}$ = –2 V |
| | $I_{D2}$ | — | — | –10 | mA | $V_{GS}$ = –1.2 V, $V_{DS}$ = –2 V |
| Drain to source breakdown voltage | $V_{(BR)\ DSS}$ | –60 | — | — | V | $I_D$ = –10 mA, $V_{GS}$ = 0 |
| Gate to source breakdown voltage | $V_{(BR)\ GSS}$ | –16 | — | — | V | $I_G$ = –100 µA, $V_{DS}$ = 0 |
| | $V_{(BR)\ GSS}$ | 3 | — | — | V | $I_G$ = 100 µA, $V_{DS}$ = 0 |
| Gate to source leak current | $I_{GSS1}$ | — | — | –100 | µA | $V_{GS}$ = –8 V, $V_{DS}$ = 0 |
| | $I_{GSS2}$ | — | — | –50 | µA | $V_{GS}$ = –3.5 V, $V_{DS}$ = 0 |
| | $I_{GSS3}$ | — | — | –1 | µA | $V_{GS}$ = –1.2 V, $V_{DS}$ = 0 |
| | $I_{GSS4}$ | — | — | 100 | µA | $V_{GS}$ = 2.4 V, $V_{DS}$ = 0 |
| Input current (shut down) | $I_{GS\ (op)\ 1}$ | — | –0.8 | — | mA | $V_{GS}$ = –8 V, $V_{DS}$ = 0 |
| | $I_{GS\ (op)\ 2}$ | — | –0.35 | — | mA | $V_{GS}$ = –3.5 V, $V_{DS}$ = 0 |
| Zero gate voltage drain current | $I_{DSS}$ | — | — | –250 | µA | $V_{DS}$ = –50 V, $V_{GS}$ = 0 |
| Gate to source cutoff voltage | $V_{GS\ (off)}$ | –1.1 | — | –2.25 | V | $I_D$ = –1 mA, $V_{DS}$ = –10 V |
| Static drain to source on state resistance | $R_{DS\ (on)}$ | — | 100 | 130 | mΩ | $I_D$ = –7.5 A, $V_{GS}$ = –4 V [Note 3] |
| | $R_{DS\ (on)}$ | — | 70 | 90 | mΩ | $I_D$ = –7.5 A, $V_{GS}$ = –10 V [Note 3] |
| Forward transfer admittance | $\|y_{fs}\|$ | 5 | 10 | — | S | $I_D$ = –7.5 A, $V_{DS}$ = –10 V [Note 3] |
| Output capacitance | Coss | — | 610 | — | pF | $V_{DS}$ = –10 V, $V_{GS}$ = 0<br>f = 1 MHz |
| Turn-on delay time | $t_{d\ (on)}$ | — | 7.5 | — | µs | $I_D$ = –7.5 A<br>$V_{GS}$ = –5 V<br>$R_L$ = 4 Ω |
| Rise time | $t_r$ | — | 36 | — | µs | |
| Turn-off delay time | $t_{d\ (off)}$ | — | 32 | — | µs | |
| Fall time | $t_f$ | — | 29 | — | µs | |
| Body-drain diode forward voltage | $V_{DF}$ | — | –1.0 | — | V | $I_F$ = –15 A, $V_{GS}$ = 0 |
| Body-drain diode reverse recovery time | $t_{rr}$ | — | 200 | — | ns | $I_F$ = –15 A, $V_{GS}$ = 0<br>$di_F/dt$ = 50 A/µs |
| Over load shut down operation time [Note4] | $t_{os1}$ | — | 3.7 | — | ms | $V_{GS}$ = –5 V, $V_{DD}$ = –12 V |
| | $t_{os2}$ | — | 1 | — | ms | $V_{GS}$ = –5 V, $V_{DD}$ = –24 V |

Notes: 3. Pulse test

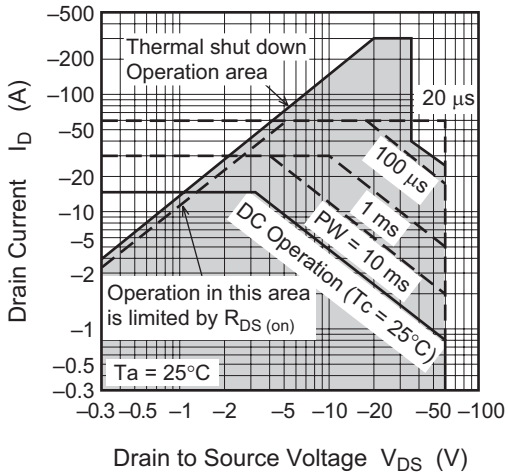
4. Include the time shift based on increasing of channel temperature when operate under over load condition.

## Main Characteristics

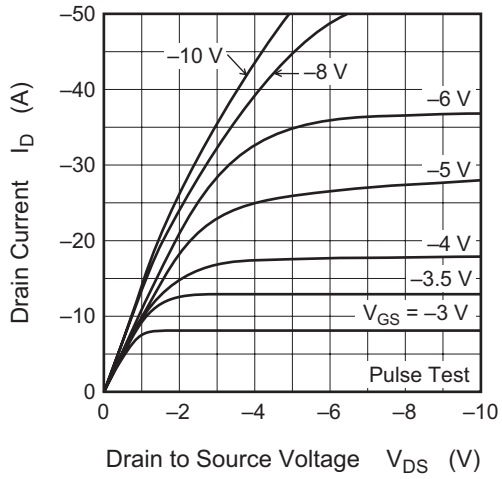
Power vs. Temperature Derating



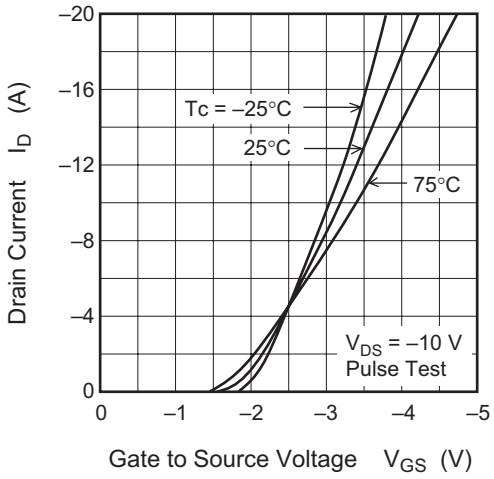

Maximum Safe Operation Area



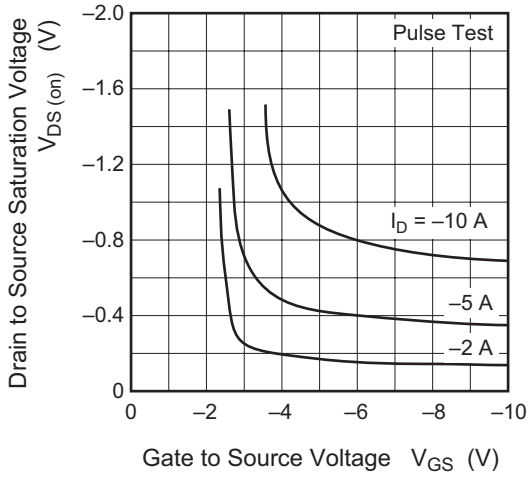

Typical Output Characteristics



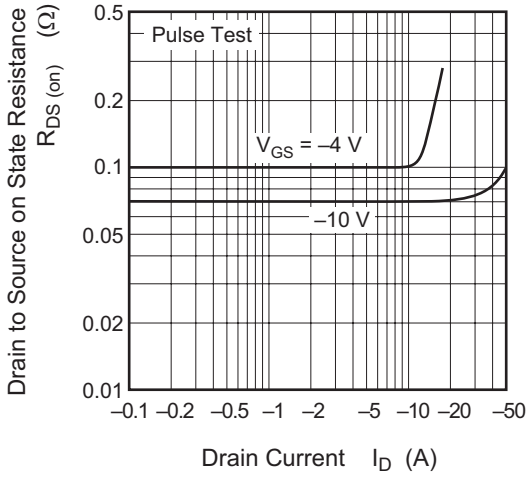

Typical Transfer Characteristics



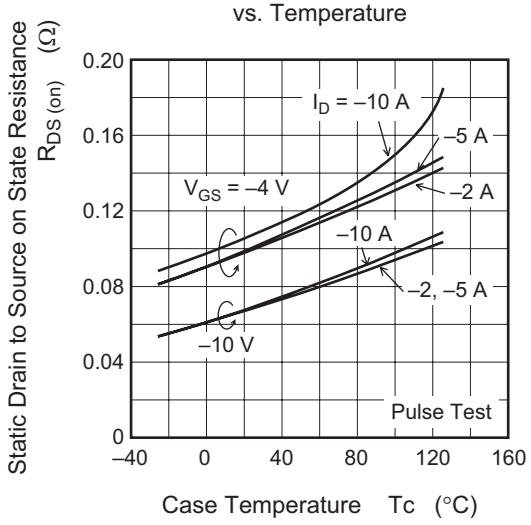

Drain to Source Saturation Voltage vs. Gate to Source Voltage



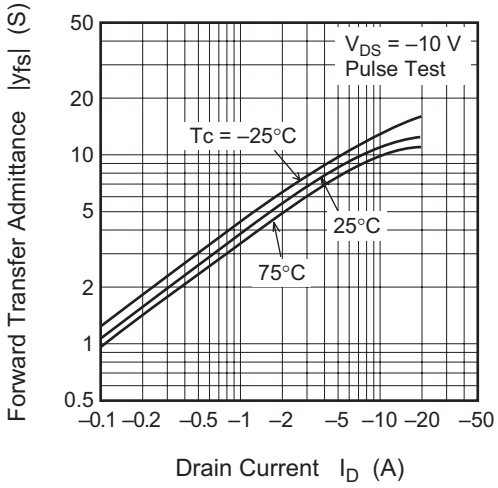

Static Drain to Source on State Resistance vs. Drain Current



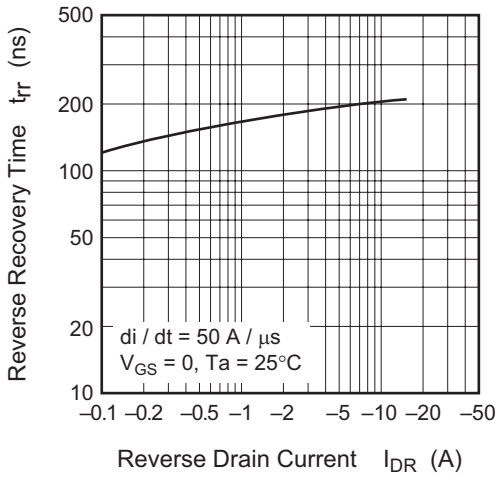
Static Drain to Source on State Resistance vs. Temperature



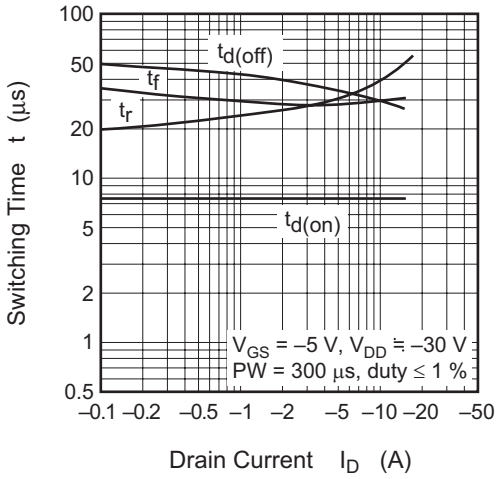

Forward Transfer Admittance vs. Drain Current



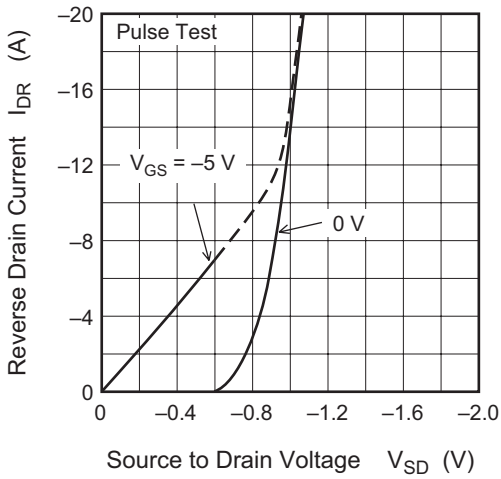

Body-Drain Diode Reverse Recovery Time



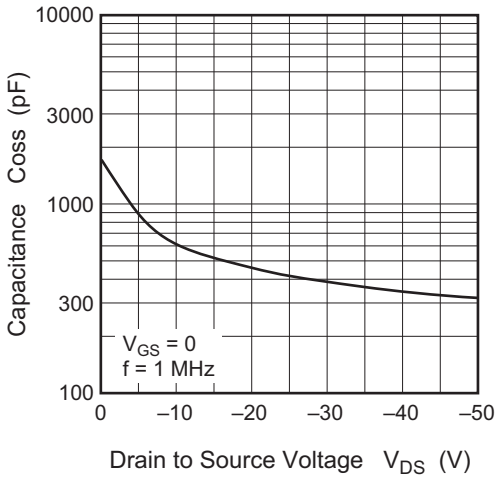

Switching Characteristics



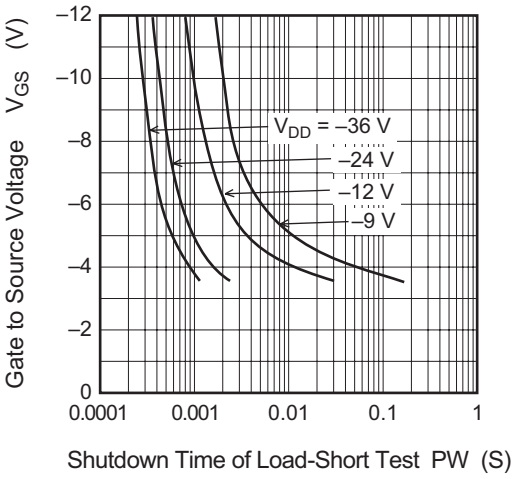

Reverse Drain Current vs. Source to Drain Voltage



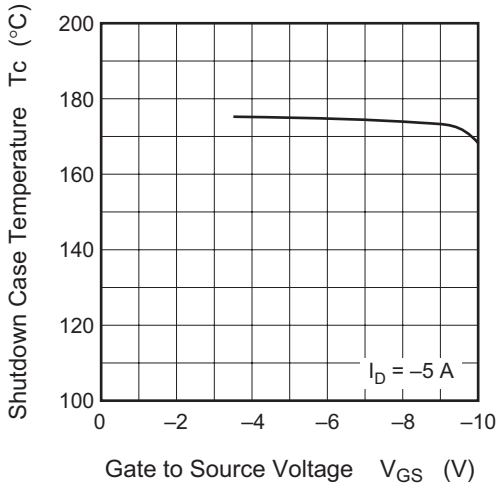

Typical Capacitance vs. Drain to Source Voltage



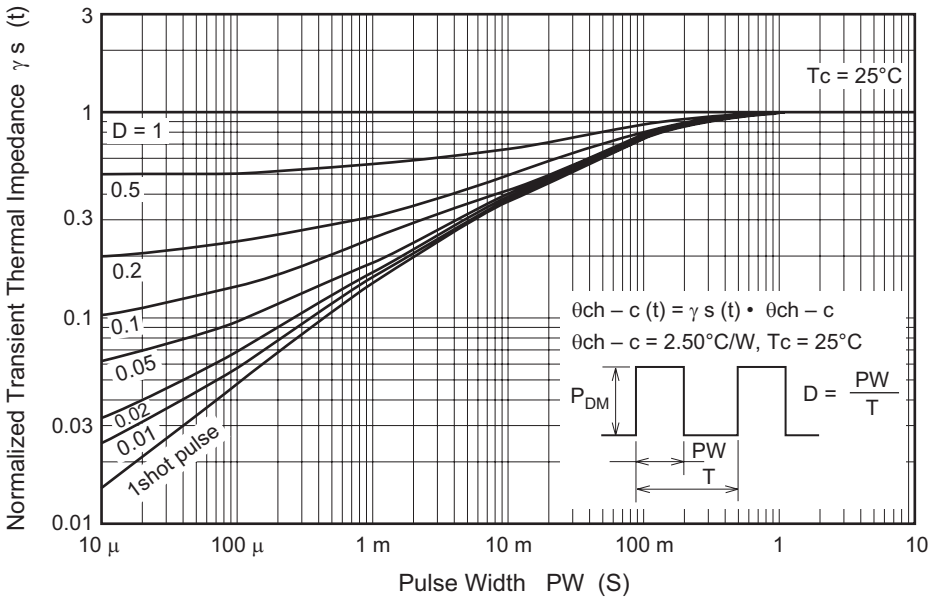
Gate to Source Voltage vs.
Shutdown Time of Load-Short Test



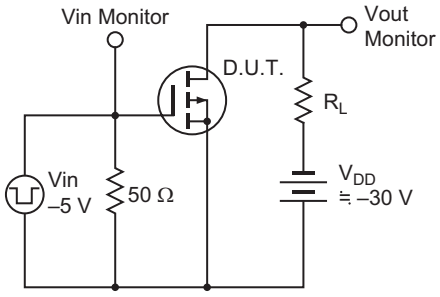

Shutdown Case Temperature vs.
Gate to Source Voltage



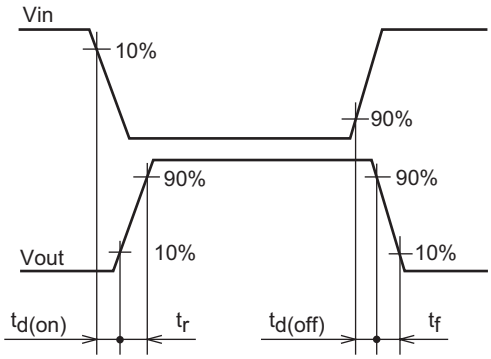

Normalized Transient Thermal Impedance vs. Pulse Width




Switching Time Test Circuit



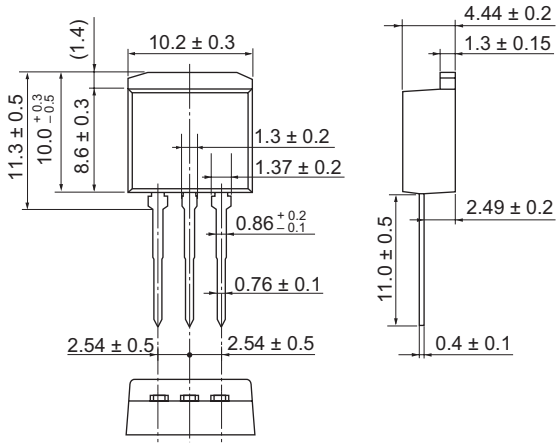

Waveform



## Package Dimensions

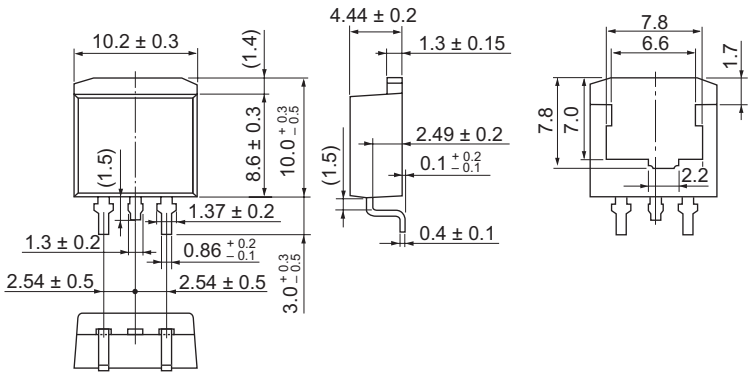
| JEITA Package Code | RENESAS Code | Package Name | MASS[Typ.] |
|---|---|---|---|
| — | PRSS0004AE-A | LDPAK(L) / LDPAK(L)V | 1.40g |

Unit: mm




| JEITA Package Code | RENESAS Code | Package Name | MASS[Typ.] |
|---|---|---|---|
| SC-83 | PRSS0004AE-B | LDPAK(S)-(1) / LDPAK(S)-(1)V | 1.30g |

Unit: mm



## Ordering Information

| Part Name | Quantity | Shipping Container |
|---|---|---|
| HAF1002-90L | Max: 50 pcs/sack | Sack |
| HAF1002-90S | Max: 50 pcs/sack | Sack |
| HAF1002-90STL | 1000 pcs/Reel | Embossed tape |
| HAF1002-90STR | 1000 pcs/Reel | Embossed tape |

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan



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http://www.renesas.com

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**Renesas Technology America, Inc.**
450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

**Renesas Technology Europe Limited**
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

**Renesas Technology Hong Kong Ltd.**
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

**Renesas Technology Taiwan Co., Ltd.**
10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

**Renesas Technology (Shanghai) Co., Ltd.**
Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

**Renesas Technology Singapore Pte. Ltd.**
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

**Renesas Technology Korea Co., Ltd.**
Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

**Renesas Technology Malaysia Sdn. Bhd.**
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510



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